

## Product Summary

|                         |                               |                          |
|-------------------------|-------------------------------|--------------------------|
| <b>BV<sub>DSS</sub></b> | <b>R<sub>DS(ON)</sub> max</b> | <b>I<sub>D</sub> max</b> |
| 50V                     | 4Ω @ V <sub>GS</sub> = 4V     | 160mA                    |

## Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- ESD Protected Gate to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

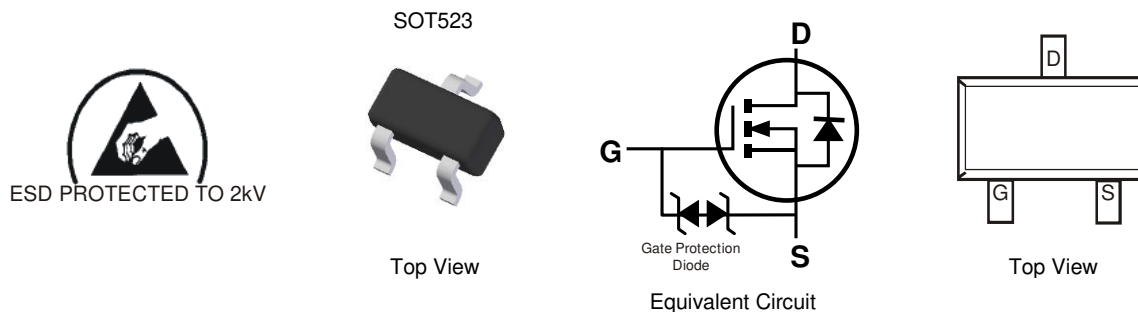
## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Driving
- Power Management Functions
- Load Switching

## Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

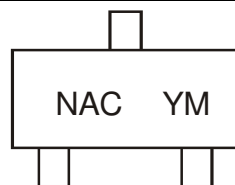


## Ordering Information (Note 4)

| Part Number | Case   | Packaging         |
|-------------|--------|-------------------|
| DMN55D0UT-7 | SOT523 | 3,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



NAC = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

### Date Code Key

| Year | 2008 | ... | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code | V    | ... | H    | I    | J    | K    | L    | M    | N    | O    | P    | R    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                    | Symbol           | Value | Unit |
|-----------------------------------|------------------|-------|------|
| Drain-Source Voltage              | V <sub>DSS</sub> | 50    | V    |
| Gate-Source Voltage               | V <sub>GSS</sub> | ±12   | V    |
| Drain Current (Note 5) Continuous | I <sub>D</sub>   | 160   | mA   |
| Pulsed Drain Current (Note 5)     | I <sub>DM</sub>  | 560   | mA   |

**Thermal Characteristics**

| Characteristic                          | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)        | P <sub>D</sub>                    | 200         | mW   |
| Thermal Resistance, Junction to Ambient | R <sub>θJA</sub>                  | 625         | °C/W |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                           | Symbol              | Min | Typ  | Max        | Unit | Test Condition   |
|--|---------------------|-----|------|------------|------|--|
| <b>OFF CHARACTERISTICS</b> (Note 6)      |                     |     |      |            |      |  |
| Drain-Source Breakdown Voltage           | BV <sub>DSS</sub>   | 50  | —    | —          | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA   |
| Zero Gate Voltage Drain Current          | I <sub>DSS</sub>    | —   | —    | 1          | μA   | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                      | I <sub>GSS</sub>    | —   | —    | 1.0<br>5.0 | μA   | V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V<br>V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V  |
| <b>ON CHARACTERISTICS</b> (Note 6)       |                     |     |      |            |      |  |
| Gate Threshold Voltage                   | V <sub>GS(TH)</sub> | 0.7 | 0.8  | 1.0        | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                   |
| Static Drain-Source On-Resistance        | R <sub>DS(ON)</sub> | —   | 3.1  | 4          | Ω    | V <sub>GS</sub> = 4V, I <sub>D</sub> = 100mA   |
|  |                     | —   | 4    | 5          |      | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 80mA  |
| Forward Transconductance                 | g <sub>FS</sub>     | 180 | —    | —          | mS   | V <sub>DS</sub> = 10V, I <sub>D</sub> = 100mA, f = 1.0kHz                                    |
| Diode Forward Voltage                    | V <sub>SD</sub>     | —   | 0.70 | 1.3        | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 100mA   |
| <b>DYNAMIC CHARACTERISTICS</b> (Note 7)  |                     |     |      |            |      |  |
| Input Capacitance                        | C <sub>iSS</sub>    | —   | 25   | —          | pF   | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz                                      |
| Output Capacitance                       | C <sub>oSS</sub>    | —   | 5    | —          | pF   |  |
| Reverse Transfer Capacitance             | C <sub>rSS</sub>    | —   | 2.1  | —          | pF   |  |
| Gate Resistance                          | R <sub>G</sub>      | —   | 500  | —          | Ω    | f = 1MHz, V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V   |
| Total Gate Charge (V <sub>GS</sub> = 4V) | Q <sub>G</sub>      | —   | 295  | —          | pC   | V <sub>DS</sub> = 10V,<br>I <sub>D</sub> = 100mA   |
| Total Gate Charge (V <sub>GS</sub> = 8V) | Q <sub>G</sub>      | —   | 636  | —          | pC   |  |
| Gate-Source Charge                       | Q <sub>GS</sub>     | —   | 72   | —          | pC   |  |
| Gate-Drain Charge                        | Q <sub>GD</sub>     | —   | 18   | —          | pC   |  |
| Turn-On Delay Time                       | t <sub>D(ON)</sub>  | —   | 6.0  | —          | ns   | V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4V,<br>R <sub>G</sub> = 25Ω, I <sub>D</sub> = 100mA |
| Turn-On Rise Time                        | t <sub>R</sub>      | —   | 4.4  | —          | ns   |  |
| Turn-Off Delay Time                      | t <sub>D(OFF)</sub> | —   | 23.4 | —          | ns   |  |
| Turn-Off Fall Time                       | t <sub>F</sub>      | —   | 11.0 | —          | ns   |  |

- Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

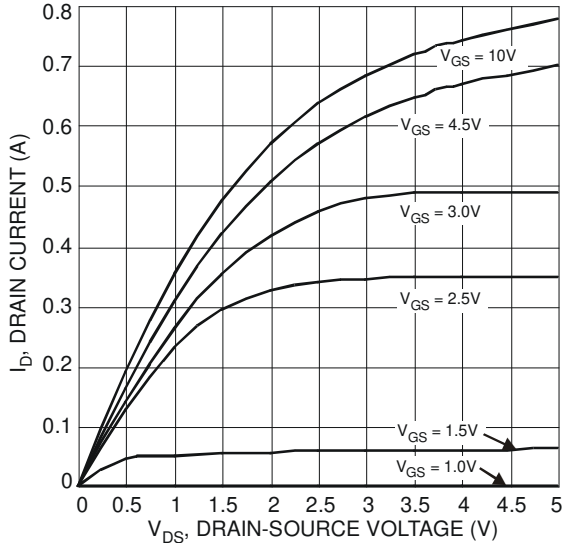


Fig. 1 Typical Output Characteristics

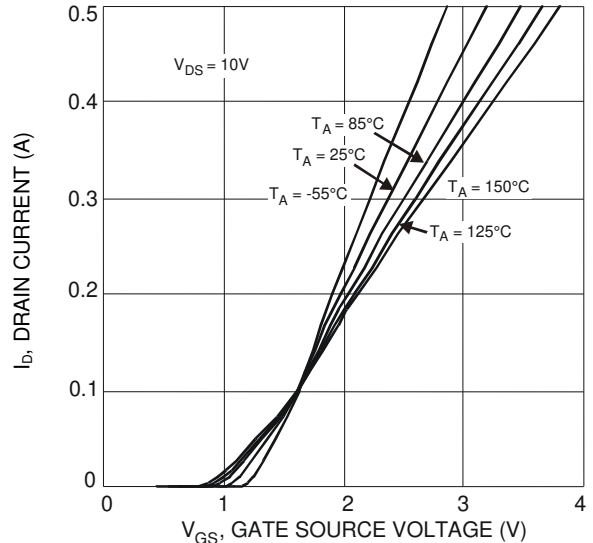


Fig. 2 Typical Transfer Characteristics

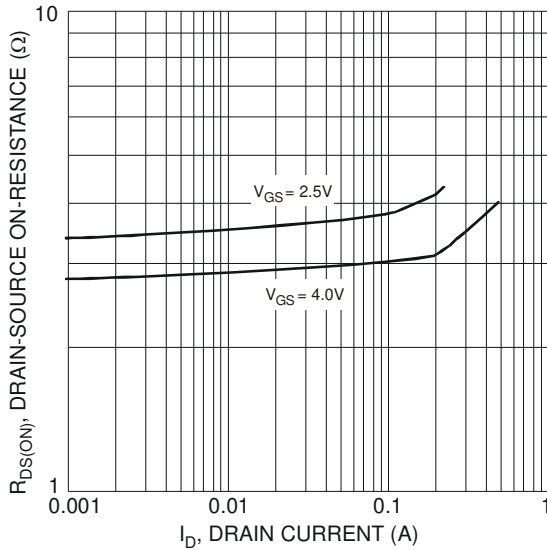


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

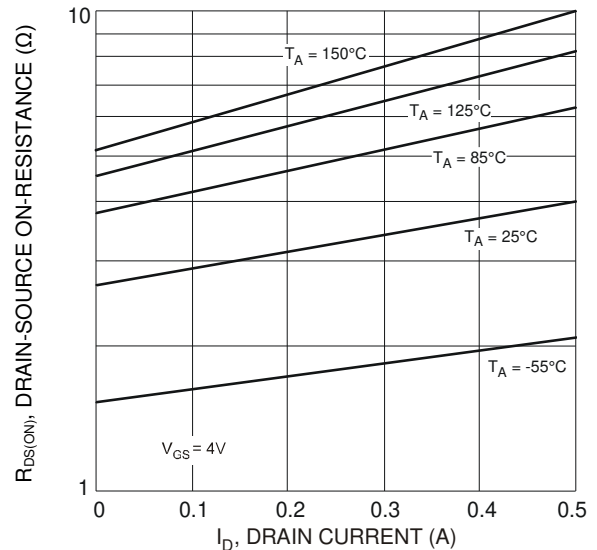


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

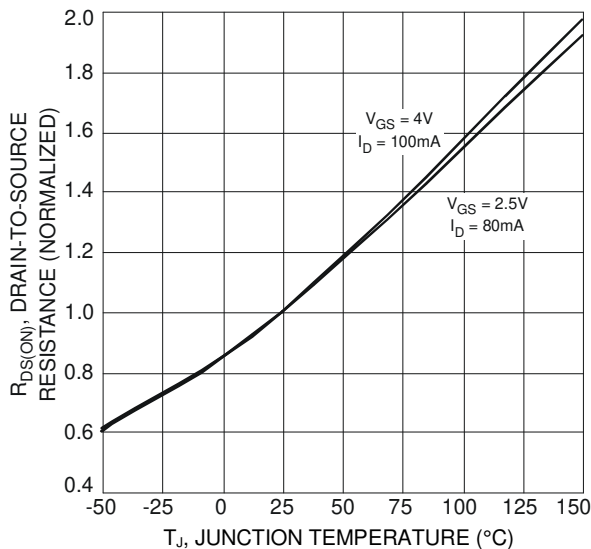


Fig. 5 On-Resistance Variation with Temperature

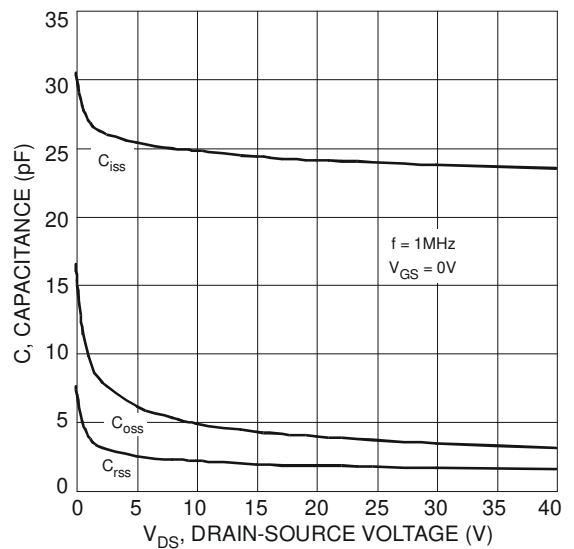


Fig. 6 Typical Capacitance

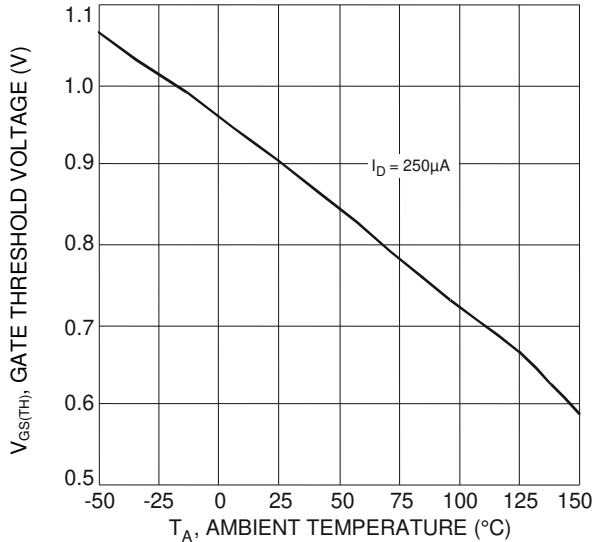


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

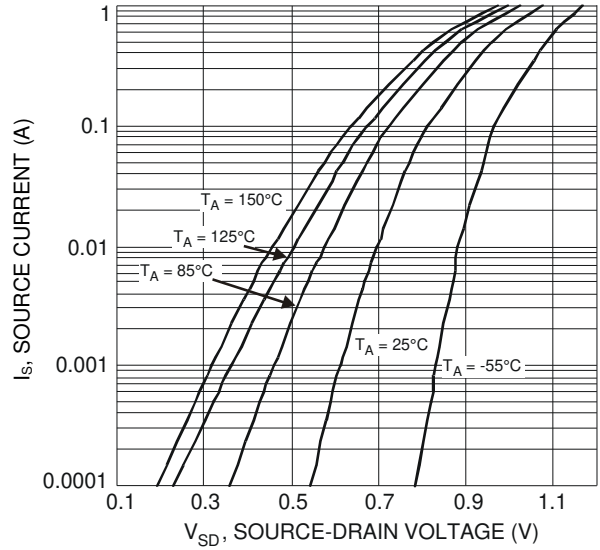


Fig. 8 Diode Forward Voltage vs. Current

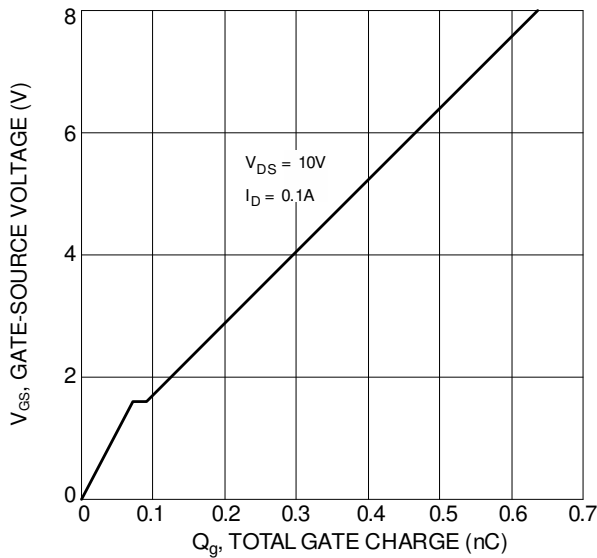


Fig. 9 Gate Charge

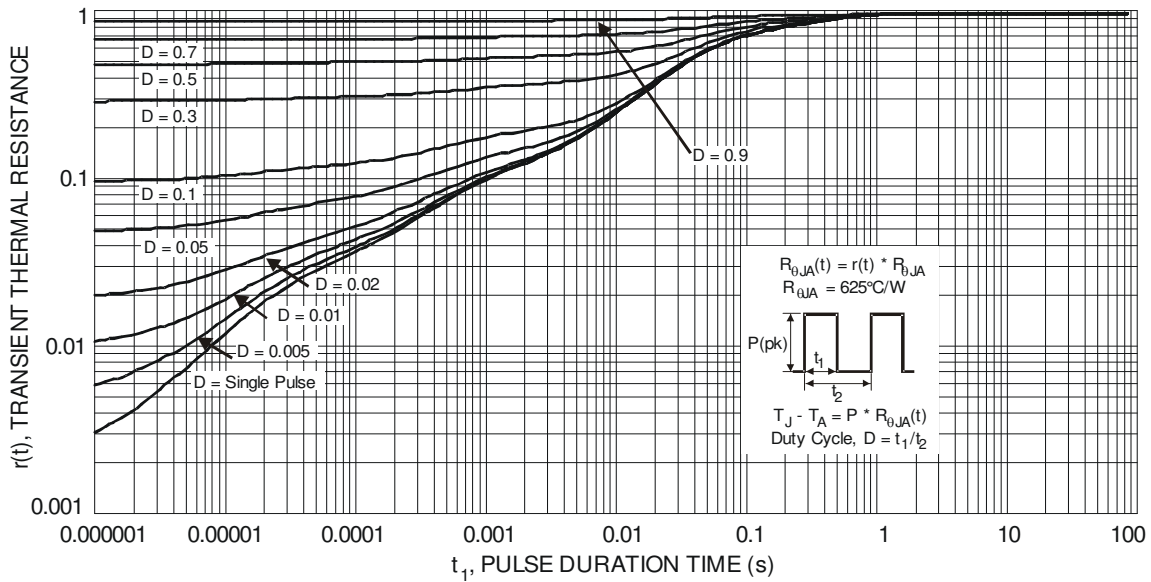
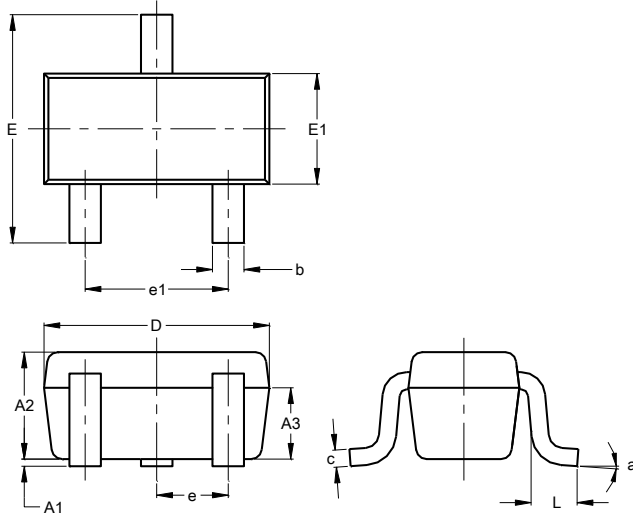


Fig. 10 Transient Thermal Response

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**

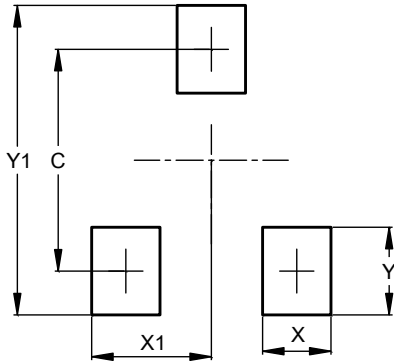


| SOT523                      |          |      |      |
|-----------------------------|----------|------|------|
| Dim                         | Min      | Max  | Typ  |
| A1                          | 0.00     | 0.10 | 0.05 |
| A2                          | 0.60     | 0.80 | 0.75 |
| A3                          | 0.45     | 0.65 | 0.50 |
| b                           | 0.15     | 0.30 | 0.22 |
| c                           | 0.10     | 0.20 | 0.12 |
| D                           | 1.50     | 1.70 | 1.60 |
| E                           | 1.45     | 1.75 | 1.60 |
| E1                          | 0.75     | 0.85 | 0.80 |
| e                           | 0.50 BSC |      |      |
| e1                          | 0.90     | 1.10 | 1.00 |
| L                           | 0.20     | 0.40 | 0.33 |
| a                           | 0°       | --   | 8°   |
| <b>All Dimensions in mm</b> |          |      |      |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 1.29          |
| X          | 0.40          |
| X1         | 0.70          |
| Y          | 0.51          |
| Y1         | 1.80          |

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